

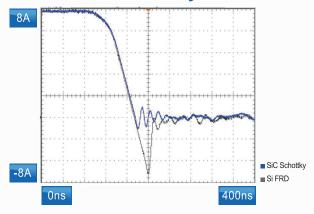


# SiC Schottky

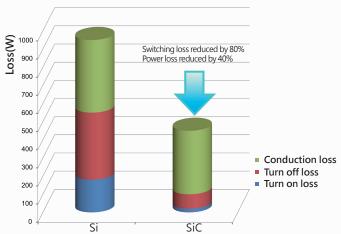
### Next generation semiconductor

Compared with silicon schottky, PanJit's new silicon carbide (SiC) schottky delivers lower switching loss, higher breakdown voltage, and outstanding performance under high temperature condition (175°C) due to its material characteristics. It is the optimal choice for customers who need high system efficiency, especially in the solar system, power management applications, and industrial fields.

#### **Reverse Recovery Loss**



### **Power Loss Comparison**

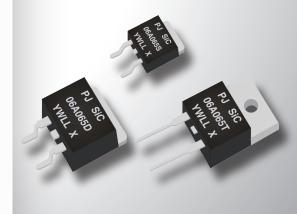


#### **Feature**

- Low Trr
- High frequency operation
- Low EMI
- Good performance at high temperature operation

## **Application**

- Industrial equipment
- Server power / PC power
- Solar inverter
- UPS
- LED







Part Number	$V_{RRM}$	I <sub>F</sub>	V <sub>F</sub> @I <sub>F</sub> Typ.	I <sub>R</sub> @V <sub>R</sub> Typ.	$Q_{C}$	Package
	V	А	V	uA	nC	
SiC02A065T	650	2	1.9	5	6	TO-220AC
SiC04A065T	650	4	1.9	6	11	
SiC06A065T	650	6	1.9	17	12	
SiC08A065T	650	8	1.9	20	15.5	
SiC10A065T	650	10	1.9	20	18	
SiC02A065S	650	2	1.9	5	6	- TO-252AA
SiC04A065S	650	4	1.9	6	11	
SiC06A065S	650	6	1.9	17	12	
SiC08A065S	650	8	1.9	20	15.5	
SiC04A065D	650	4	1.9	6	11	TO-263/D <sup>2</sup> PAK
SiC06A065D	650	6	1.9	17	12	
SiC08A065D	650	8	1.9	20	15.5	
SiC10A065D	650	10	1.9	20	18	

<sup>■</sup> All data are subject to change.
Please visit www.panjit.com or contact sales@panjit.com.tw for updates.